

MR1035-820

forming a dielectric layer used as an inter-layer dielectric on said semiconductor substrate;

D' lapping said dielectric layer by means of a chemical mechanical polishing;  
and

forming on said lapped dielectric layer a cap layer of silicon nitrogen-oxide to have a refractive index of at least 1.6, wherein said cap layer is translucent to ultra-violet light.

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9. (Four Times Amended) A planarization method of inter-metal dielectrics, comprising the steps of:

D2 providing a semiconductor substrate having a plurality of metal-interconnects formed thereon;

forming a dielectric layer used as an inter-metal dielectric on said substrate;  
lapping said dielectric layer by means of a chemical mechanical polishing;  
and

forming on said lapped dielectric layer a cap layer of silicon nitrogen-oxide to have a refractive index of at least 1.6, wherein said cap layer is translucent to ultra-violet light.

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